

5 V Differential PECL to TTL Translator

MC10ELT21, MC100ELT21

Description

The MC10ELT/100ELT21 is a differential PECL to TTL translator. Because PECL (Positive ECL) levels are used, only +5 V and ground are required. The small outline 8-lead package and the single gate of the ELT21 makes it ideal for those applications where space, performance and low power are at a premium.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a 0.01 μ F capacitor and limit current sourcing or sinking to 0.5 mA. When not used, V_{BB} should be left open.

The 100 Series contains temperature compensation.

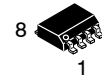
Features

- 3.5 ns Typical Propagation Delay
- 24 mA TTL Output
- Flow Through Pinouts
- Operating Range: $V_{CC} = 4.75$ V to 5.25 V with GND = 0 V
- Q Output Will Default LOW with Inputs Left Open or < 1.3 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



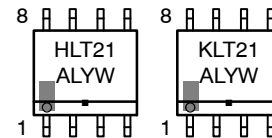
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SOIC-8
D SUFFIX
CASE
751-07

MARKING DIAGRAMS*



H = MC10
K = MC100
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note [AND8002/D](#).

ORDERING INFORMATION

Device	Package	Shipping†
MC10ELT21DG	SOIC-8 (Pb-Free)	98 Units / Tube
MC10ELT21DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC100ELT21DG	SOIC-8 (Pb-Free)	98 Units / Tube

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

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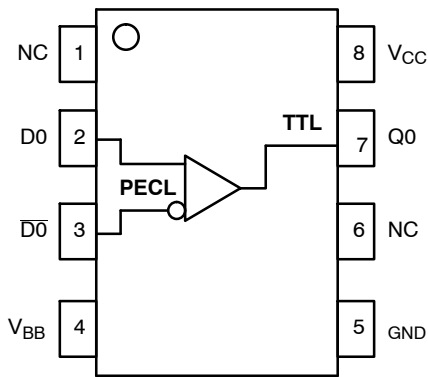


Figure 1. 8-Lead Pinout and Logic Diagram
(Top View)

Table 1. PIN DESCRIPTION

Pin	Function
Q0	TTL Outputs
D0, $\overline{D0}$	PECL Differential Outputs
V_{BB}	Reference Voltage Output
V_{CC}	Positive Supply
GND	Ground
NC	No Connect

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	50 k Ω
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model	> 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	81 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note [AND8003/D](#).

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Power Supply	GND = 0 V		7	V
V_{IN}	PECL Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	0 to 6	V
I_{BB}	V_{BB} Sink/Source			± 0.5	mA
TA	Operating Temperature Range			-40 to +85	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range			-65 to +150	$^{\circ}\text{C}$
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 SOIC-8	190 130	$^{\circ}\text{C}/\text{W}$ $^{\circ}\text{C}/\text{W}$
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8	41 to 44	$^{\circ}\text{C}/\text{W}$
T_{sol}	Wave Solder	Pb-Free	<2 to 3 sec @ 260 $^{\circ}\text{C}$	265	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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Table 4. 10ELT SERIES PECL INPUT DC CHARACTERISTICS $V_{CC} = 5.0\text{ V}$; $GND = 0.0\text{ V}$ (Note 2)

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{IH}	Input HIGH Voltage (Single-Ended)	3770		4110	3870		4190	3930		4265	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3050		3500	3050		3520	3050		3555	mV
V_{BB}	Output Voltage Reference	3.57		3.7	3.65		3.75	3.69		3.81	V
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.2		5.0	2.2		5.0	2.2		5.0	V
I_{IH}	Input HIGH Current			255			175			175	μA
I_{IL}	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

2. Output parameters vary 1:1 with V_{CC} . V_{CC} can vary $\pm 0.25\text{ V}$.
3. V_{IHCMR} min varies 1:1 with GND , V_{IHCMR} max varies 1:1 with V_{CC} .

Table 5. 100ELT SERIES PECL INPUT DC CHARACTERISTICS $V_{CC} = 5.0\text{ V}$; $GND = 0.0\text{ V}$ (Note 4)

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{IH}	Input HIGH Voltage (Single-Ended)	3835		4120	3835		4120	3835		4120	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3190		3525	3190		3525	3190		3525	mV
V_{BB}	Output Voltage Reference	3.62		3.74	3.62		3.74	3.62		3.745	V
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 5)	2.2		5.0	2.2		5.0	2.2		5.0	V
I_{IH}	Input HIGH Current			255			175			175	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

4. Input parameters vary 1:1 with V_{CC} . V_{CC} can vary $\pm 0.25\text{ V}$.
5. V_{IHCMR} min varies 1:1 with GND , V_{IHCMR} max varies 1:1 with V_{CC} .

Table 6. TTL OUTPUT DC CHARACTERISTICS $V_{CC} = 4.75\text{ V}$ to 5.25 V ; $T_A = -40^\circ\text{C}$ to 85°C)

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
V_{OH}	Output HIGH Voltage	$I_{OH} = -3.0\text{ mA}$	2.4		(Note 6)	V
V_{OL}	Output LOW Voltage	$I_{OL} = 24\text{ mA}$			0.5	V
I_{CCH}	Power Supply Current			20	29	mA
I_{CCL}	Power Supply Current			22	32	mA
I_{OS}	Output Short Circuit Current		-150		-60	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

6. Maximum level is $V_{CC} - 0.7$ by design.

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AC CHARACTERISTICS $V_{CC} = 4.75\text{ V to }5.25\text{ V}$; $GND = 0.0\text{ V}$ (Note 7)

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{\max}	Maximum Toggle Frequency					100					MHz
t_{JITTER}	Random Clock Jitter (RMS)					35					ps
t_{PLH}	Propagation Delay @ 1.5 V	2.0		5.5	2.0		5.5	2.0		5.5	ns
t_{PHL}	Propagation Delay @ 1.5 V	2.0		5.5	2.0		5.5	2.0		5.5	ns
V_{PP}	Input Swing (Note 8)	200		1000	200		1000	200		1000	mV
t_r/t_f	Output Rise/Fall Time (10–90%)					750					ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

7. $R_L = 500\ \Omega$ to GND and $C_L = 20\text{ pF}$ to GND. Refer to Figure 2.

8. $V_{\text{PP}(\text{min})}$ is the minimum input swing for which AC parameters are guaranteed. The device has a DC gain of ≈ 40 .

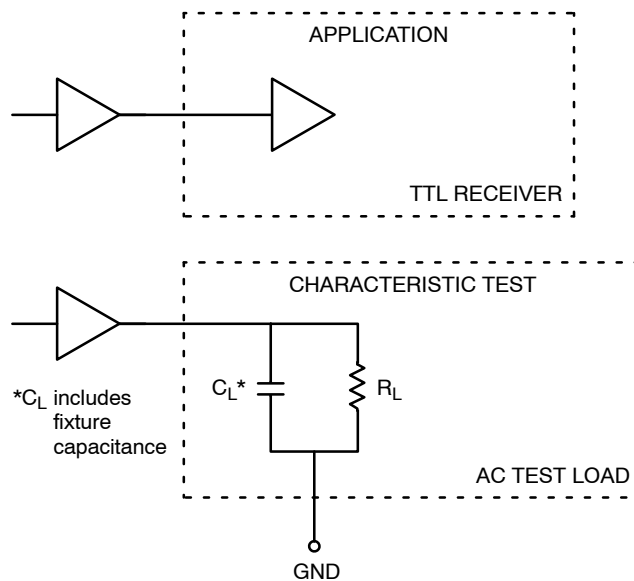


Figure 2. TTL Output Loading Used for Device Evaluation

Resource Reference of Application Notes

- AN1405/D** – ECL Clock Distribution Techniques
- AN1406/D** – Designing with PECL (ECL at +5.0 V)
- AN1503/D** – ECLinPS™ I/O SPICE Modeling Kit
- AN1504/D** – Metastability and the ECLinPS Family
- AN1568/D** – Interfacing Between LVDS and ECL
- AN1672/D** – The ECL Translator Guide
- AND8001/D** – Odd Number Counters Design
- AND8002/D** – Marking and Date Codes
- AND8020/D** – Termination of ECL Logic Devices
- AND8066/D** – Interfacing with ECLinPS
- AND8090/D** – AC Characteristics of ECL Devices

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week
 ■ = Pb-Free Package

XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|--|---|---|---|
| <p>STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. COLLECTOR
 4. EMITTER
 5. EMITTER
 6. BASE
 7. BASE
 8. EMITTER</p> | <p>STYLE 2:
 PIN 1. COLLECTOR, DIE, #1
 2. COLLECTOR, #1
 3. COLLECTOR, #2
 4. COLLECTOR, #2
 5. BASE, #2
 6. EMITTER, #2
 7. BASE, #1
 8. EMITTER, #1</p> | <p>STYLE 3:
 PIN 1. DRAIN, DIE #1
 2. DRAIN, #1
 3. DRAIN, #2
 4. DRAIN, #2
 5. GATE, #2
 6. SOURCE, #2
 7. GATE, #1
 8. SOURCE, #1</p> | <p>STYLE 4:
 PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. ANODE
 5. ANODE
 6. ANODE
 7. ANODE
 8. COMMON CATHODE</p> |
| <p>STYLE 5:
 PIN 1. DRAIN
 2. DRAIN
 3. DRAIN
 4. DRAIN
 5. GATE
 6. GATE
 7. SOURCE
 8. SOURCE</p> | <p>STYLE 6:
 PIN 1. SOURCE
 2. DRAIN
 3. DRAIN
 4. SOURCE
 5. SOURCE
 6. GATE
 7. GATE
 8. SOURCE</p> | <p>STYLE 7:
 PIN 1. INPUT
 2. EXTERNAL BYPASS
 3. THIRD STAGE SOURCE
 4. GROUND
 5. DRAIN
 6. GATE 3
 7. SECOND STAGE Vd
 8. FIRST STAGE Vd</p> | <p>STYLE 8:
 PIN 1. COLLECTOR, DIE #1
 2. BASE, #1
 3. BASE, #2
 4. COLLECTOR, #2
 5. COLLECTOR, #2
 6. EMITTER, #2
 7. EMITTER, #1
 8. COLLECTOR, #1</p> |
| <p>STYLE 9:
 PIN 1. EMITTER, COMMON
 2. COLLECTOR, DIE #1
 3. COLLECTOR, DIE #2
 4. EMITTER, COMMON
 5. EMITTER, COMMON
 6. BASE, DIE #2
 7. BASE, DIE #1
 8. EMITTER, COMMON</p> | <p>STYLE 10:
 PIN 1. GROUND
 2. BIAS 1
 3. OUTPUT
 4. GROUND
 5. GROUND
 6. BIAS 2
 7. INPUT
 8. GROUND</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. DRAIN 2
 7. DRAIN 1
 8. DRAIN 1</p> | <p>STYLE 12:
 PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 13:
 PIN 1. N.C.
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> | <p>STYLE 14:
 PIN 1. N-SOURCE
 2. N-GATE
 3. P-SOURCE
 4. P-GATE
 5. P-DRAIN
 6. P-DRAIN
 7. N-DRAIN
 8. N-DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE 1
 2. ANODE 1
 3. ANODE 1
 4. ANODE 1
 5. CATHODE, COMMON
 6. CATHODE, COMMON
 7. CATHODE, COMMON
 8. CATHODE, COMMON</p> | <p>STYLE 16:
 PIN 1. EMITTER, DIE #1
 2. BASE, DIE #1
 3. EMITTER, DIE #2
 4. BASE, DIE #2
 5. COLLECTOR, DIE #2
 6. COLLECTOR, DIE #2
 7. COLLECTOR, DIE #1
 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17:
 PIN 1. VCC
 2. V2OUT
 3. V1OUT
 4. TXE
 5. RXE
 6. VEE
 7. GND
 8. ACC</p> | <p>STYLE 18:
 PIN 1. ANODE
 2. ANODE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. CATHODE
 8. CATHODE</p> | <p>STYLE 19:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. MIRROR 2
 7. DRAIN 1
 8. MIRROR 1</p> | <p>STYLE 20:
 PIN 1. SOURCE (N)
 2. GATE (N)
 3. SOURCE (P)
 4. GATE (P)
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 21:
 PIN 1. CATHODE 1
 2. CATHODE 2
 3. CATHODE 3
 4. CATHODE 4
 5. CATHODE 5
 6. COMMON ANODE
 7. COMMON ANODE
 8. CATHODE 6</p> | <p>STYLE 22:
 PIN 1. I/O LINE 1
 2. COMMON CATHODE/VCC
 3. COMMON CATHODE/VCC
 4. I/O LINE 3
 5. COMMON ANODE/GND
 6. I/O LINE 4
 7. I/O LINE 5
 8. COMMON ANODE/GND</p> | <p>STYLE 23:
 PIN 1. LINE 1 IN
 2. COMMON ANODE/GND
 3. COMMON ANODE/GND
 4. LINE 2 IN
 5. LINE 2 OUT
 6. COMMON ANODE/GND
 7. COMMON ANODE/GND
 8. LINE 1 OUT</p> | <p>STYLE 24:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR/ANODE
 4. COLLECTOR/ANODE
 5. CATHODE
 6. CATHODE
 7. COLLECTOR/ANODE
 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25:
 PIN 1. VIN
 2. N/C
 3. REXT
 4. GND
 5. IOUT
 6. IOUT
 7. IOUT
 8. IOUT</p> | <p>STYLE 26:
 PIN 1. GND
 2. dv/dt
 3. ENABLE
 4. ILIMIT
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. VCC</p> | <p>STYLE 27:
 PIN 1. ILIMIT
 2. OVLO
 3. UVLO
 4. INPUT+
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. DRAIN</p> | <p>STYLE 28:
 PIN 1. SW_TO_GND
 2. DASIC OFF
 3. DASIC_SW_DET
 4. GND
 5. V_MON
 6. VBULK
 7. VBULK
 8. VIN</p> |
| <p>STYLE 29:
 PIN 1. BASE, DIE #1
 2. EMITTER, #1
 3. BASE, #2
 4. EMITTER, #2
 5. COLLECTOR, #2
 6. COLLECTOR, #2
 7. COLLECTOR, #1
 8. COLLECTOR, #1</p> | <p>STYLE 30:
 PIN 1. DRAIN 1
 2. DRAIN 1
 3. GATE 2
 4. SOURCE 2
 5. SOURCE 1/DRAIN 2
 6. SOURCE 1/DRAIN 2
 7. SOURCE 1/DRAIN 2
 8. GATE 1</p> | | |

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